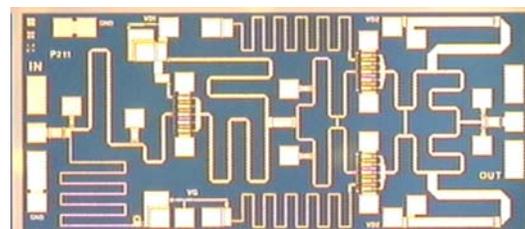


### FEATURES

- 9.5 – 12.0 GHz Operating Frequency Range
- 27.0dBm Output Power at 1dB Compression
- 17.0 dB Typical Small Signal Gain
- -40dBc OIMD3 @Each Tone Pout 17dBm

### APPLICATIONS

- Point-to-point and point-to-multipoint radio
- Military Radar Systems



Dimension: 2500um X 1130um  
Thickness: 75um ± 13um



Caution! ESD sensitive device.

### ELECTRICAL CHARACTERISTICS (T<sub>a</sub> = 25 °C, 50 ohm, VDD=7V, IDQ=380mA)

SYMBOL	PARAMETER/TEST CONDITIONS	MIN	TYP	MAX	UNITS
F	Operating Frequency Range	9.5		12.0	GHz
P1dB	Output Power at 1dB Gain Compression	25.5	27.0		dBm
Gss	Small Signal Gain	14.0	17.0		dB
OIMD3	Output 3 <sup>rd</sup> Order Intermodulation Distortion @Δf=10MHz, Each Tone Pout 17dBm		-40	-37	dBc
Input RL	Input Return Loss		-10	-7	dB
Output RL	Output Return Loss		-10	-7	dB
Idss	Saturate Drain Current V <sub>DS</sub> =3V, V <sub>GS</sub> =0V	460	619	700	mA
V <sub>DD</sub>	Power Supply Voltage		7	8	V
R <sub>th</sub>	Thermal Resistance (Au-Sn Eutectic Attach)		15		°C/W
T <sub>b</sub>	Operating Base Plate Temperature	-35		+85	°C

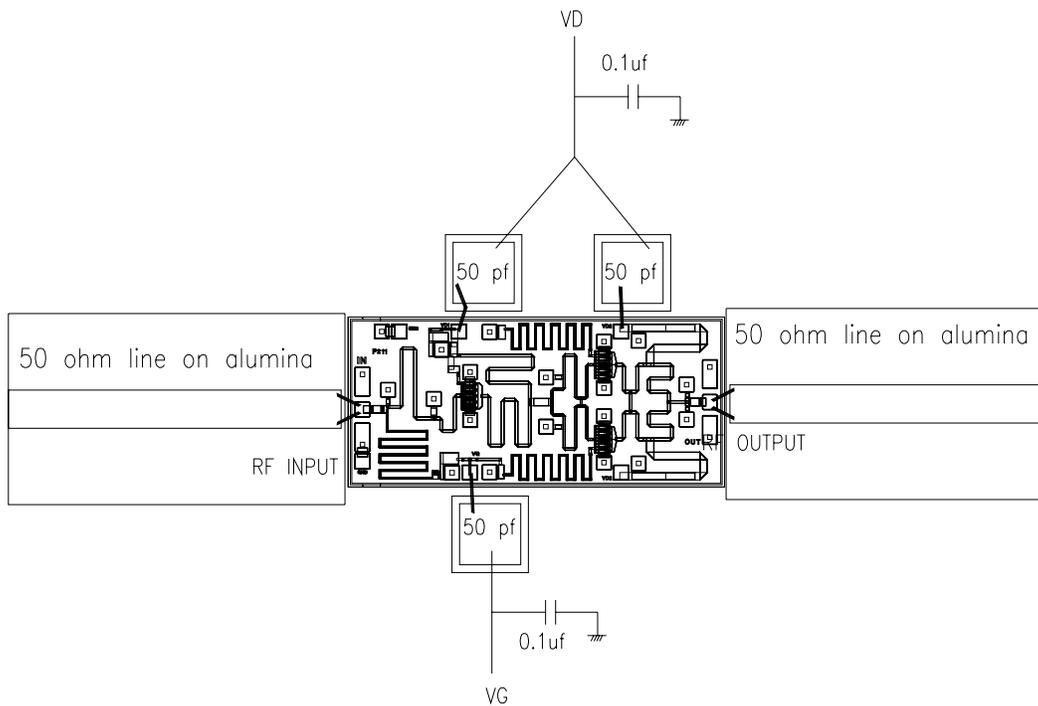
### ABSOLUTE MAXIMUM RATINGS FOR CONTINUOUS OPERATION<sup>1,2</sup>

SYMBOL	CHARACTERISTIC	VALUE
V <sub>DS</sub>	Drain to Source Voltage	8 V
V <sub>GS</sub>	Gate to Source Voltage	-4 V
I <sub>DD</sub>	Drain Current	Idss
I <sub>GSF</sub>	Forward Gate Current	7.5mA
P <sub>IN</sub>	Input Power	@ 3dB compression
T <sub>CH</sub>	Channel Temperature	150°C
T <sub>STG</sub>	Storage Temperature	-65/150°C
P <sub>T</sub>	Total Power Dissipation	7.9W

1. Operating the device beyond any of the above rating may result in permanent damage.

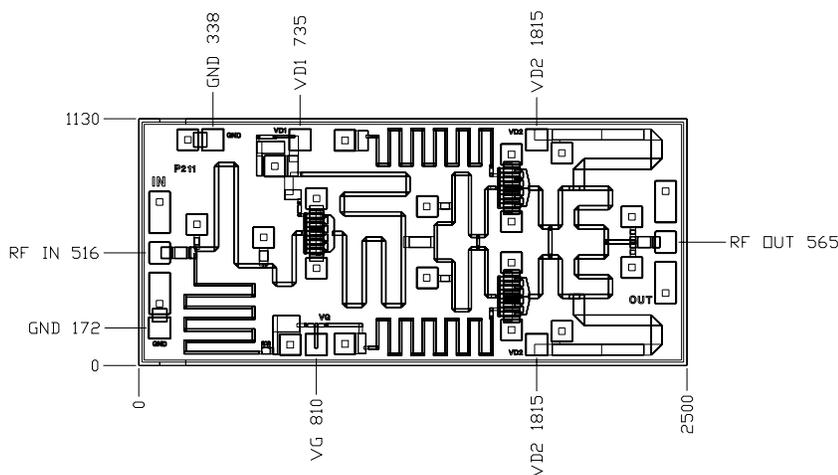
2. Bias conditions must also satisfy the following equation  $V_{DS} \cdot I_{DS} < (T_{CH} - T_{HS})/R_{TH}$ ; where T<sub>HS</sub> = ambient temperature

### ASSEMBLY DRAWING



The length of RF wires should be as short as possible. Use at least two wires between RF pad and 50 ohm line and separate the wires to minimize the mutual inductance.

### CHIP OUTLINE



Chip Size 1130 x 2500 microns  
Chip Thickness: 75 ± 13 microns  
PAD Dimensions: 100 x 100 microns  
All Dimensions in Microns

Specifications are subject to change without notice.

Excelics Semiconductor, Inc. 310 De Guigne Drive, Sunnyvale, CA 94085  
Phone: 408-737-1711 Fax: 408-737-1868 Web: [www.excelics.com](http://www.excelics.com)

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